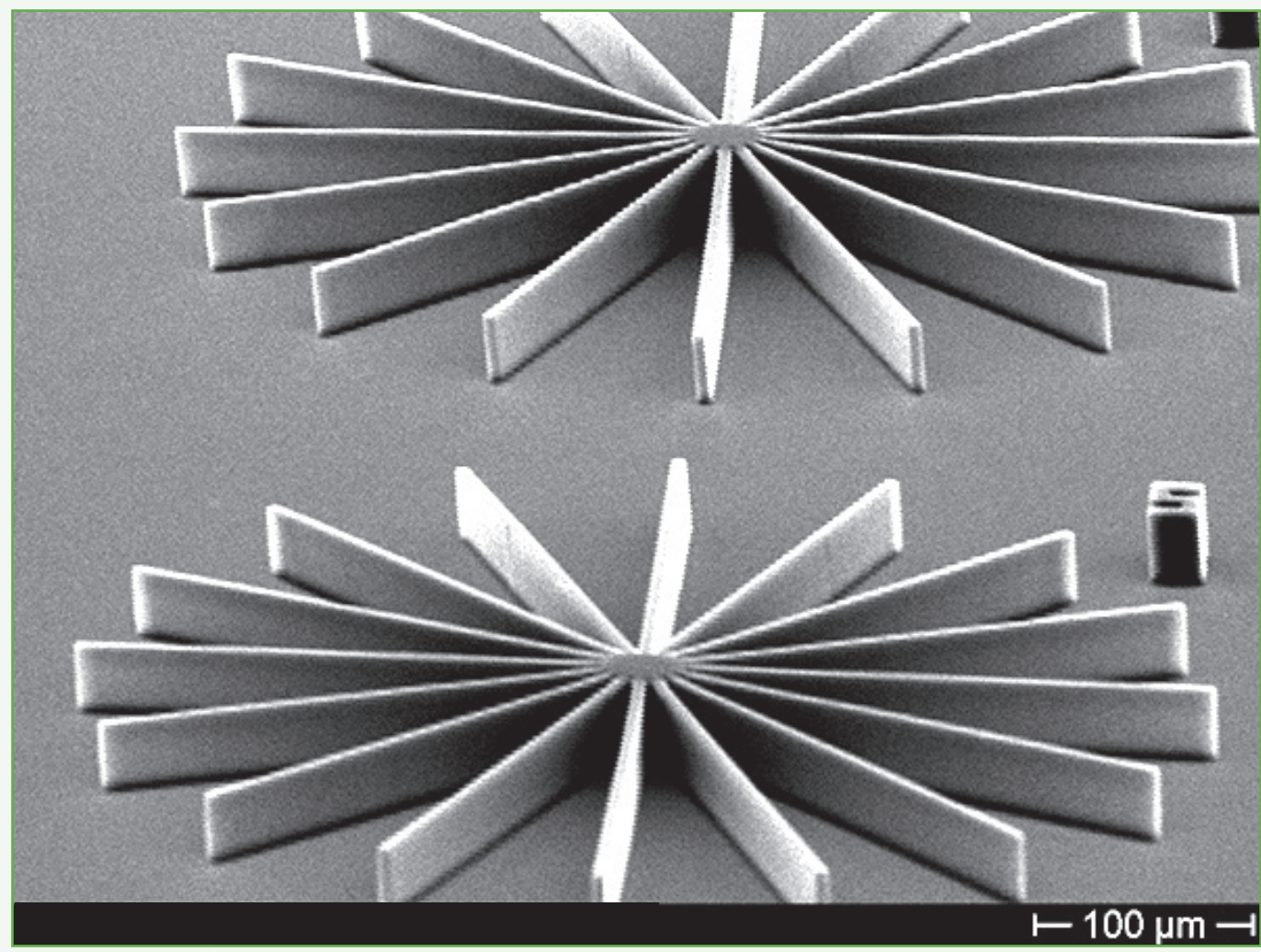


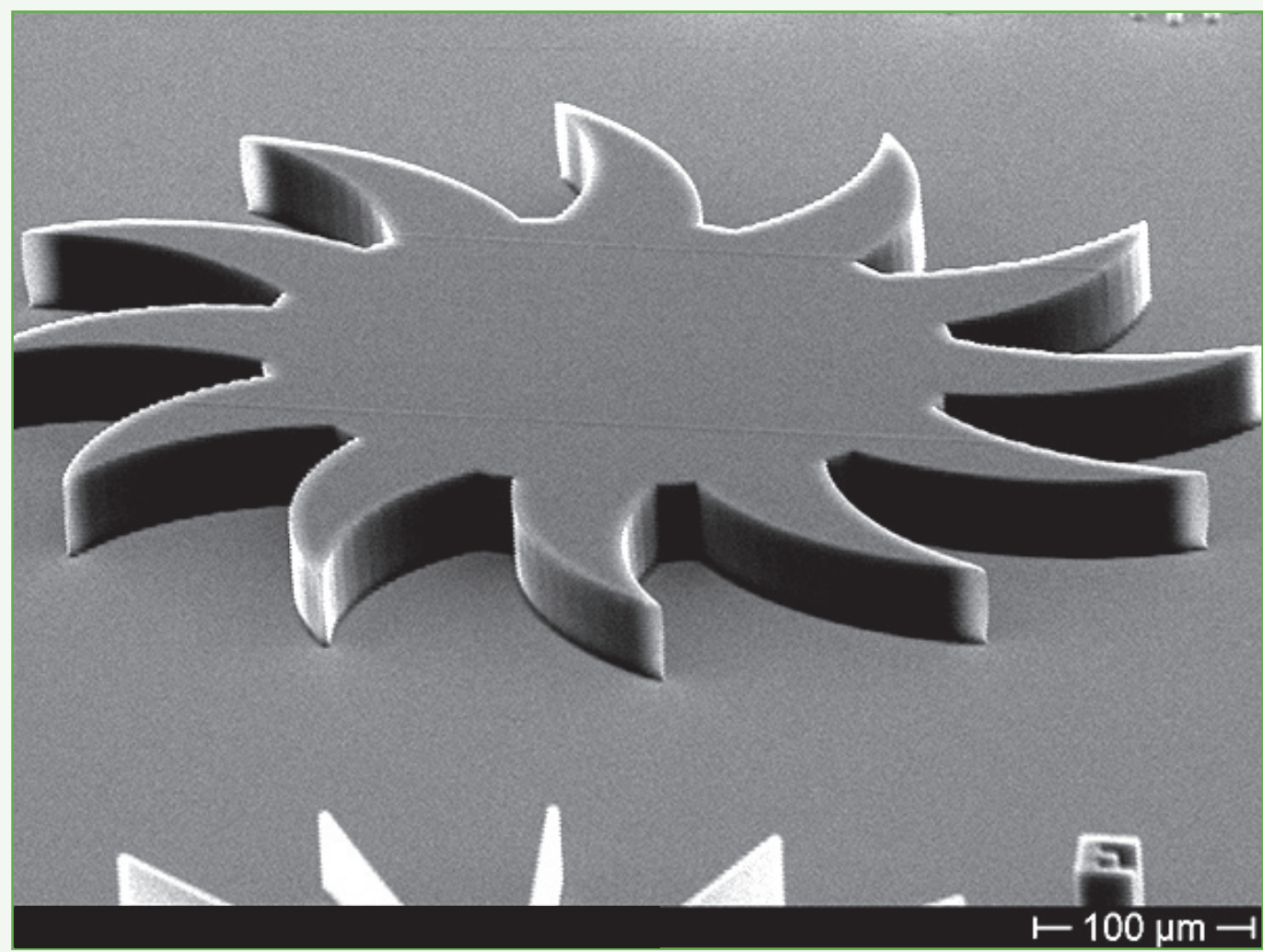
# mr-DWL — Negative Tone Photoresist Series

For Direct Laser Writing (DLW) @ 405 nm & Two Photon Polymerization (2PP)

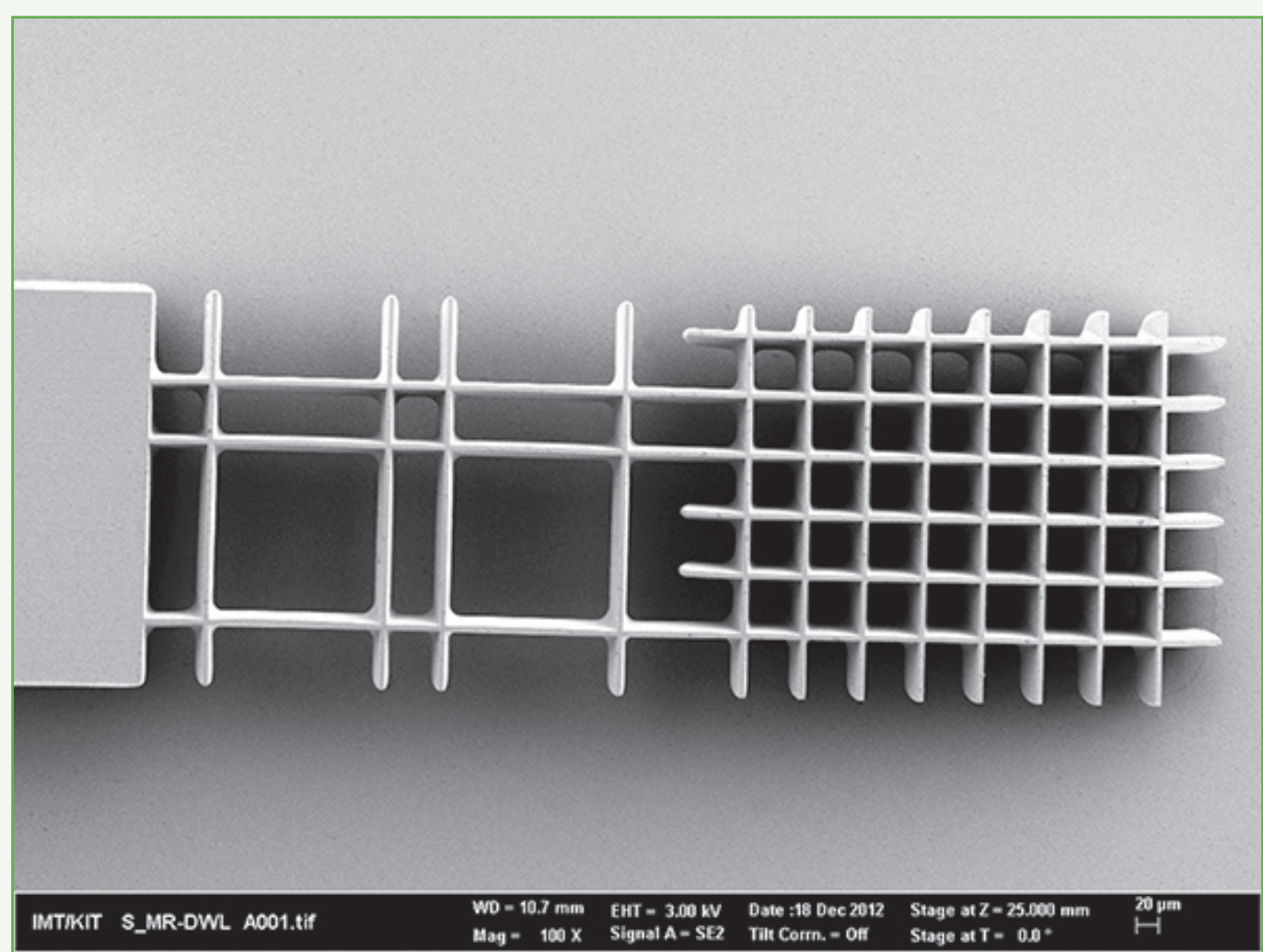
## DLW



Film thickness 50  $\mu\text{m}$ , 5  $\mu\text{m}$  Star pattern, AR: 10

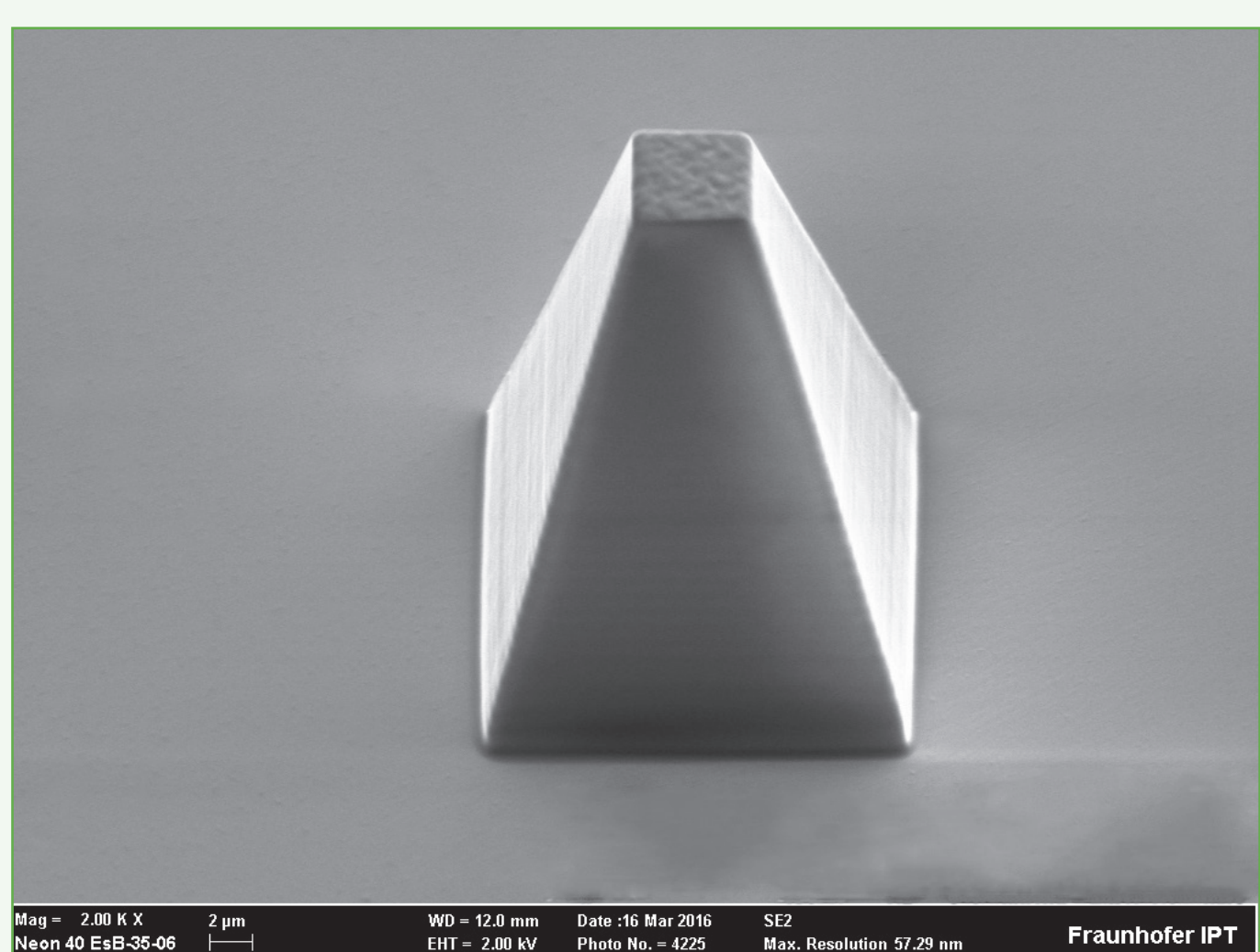


Film thickness 50  $\mu\text{m}$ , wheel pattern

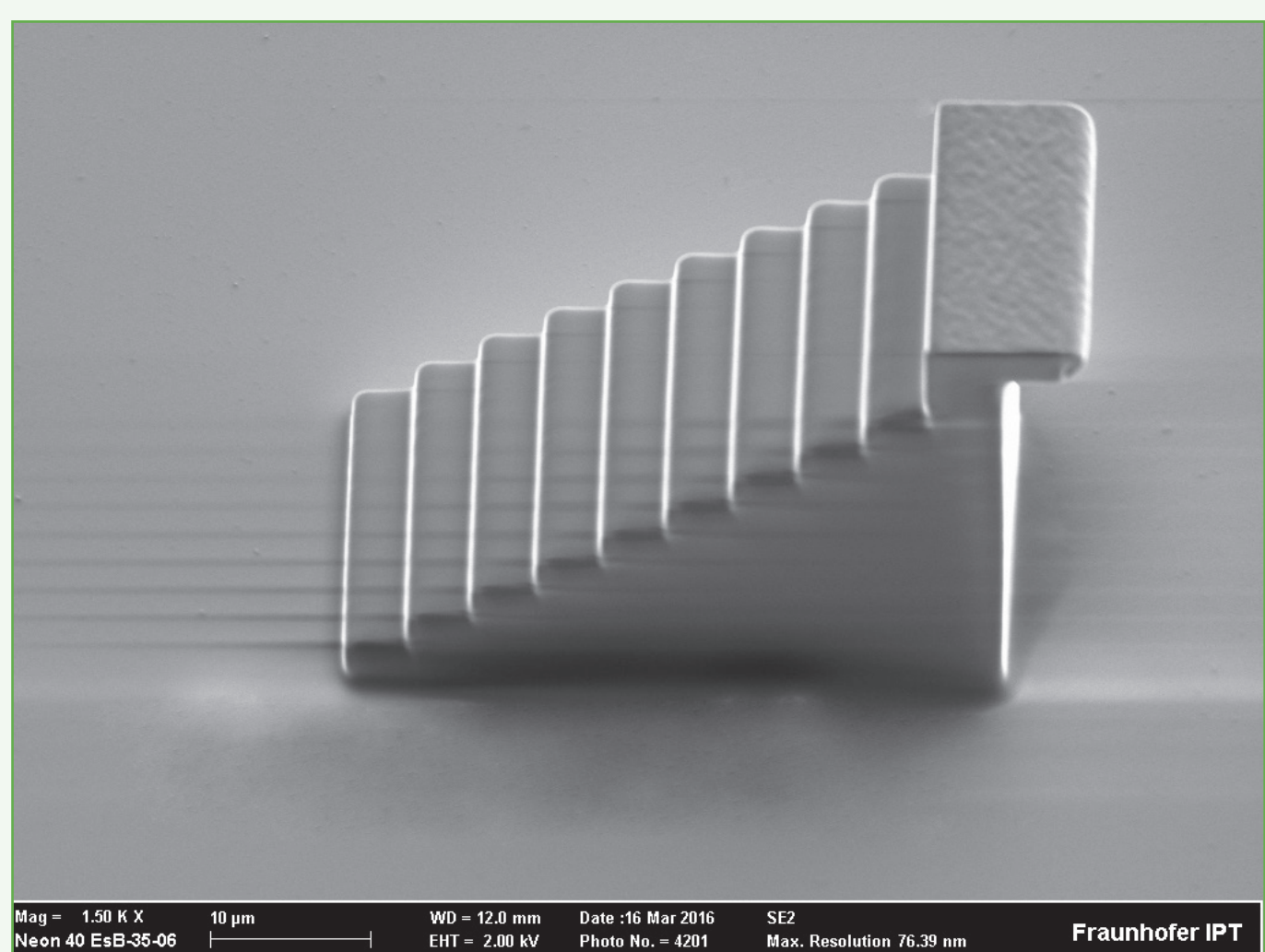


Film thickness 150  $\mu\text{m}$ , AR:  $\geq 10^1$

## 2PP



40  $\mu\text{m}$  thick mr-DWL, pyramid pattern <sup>2</sup>

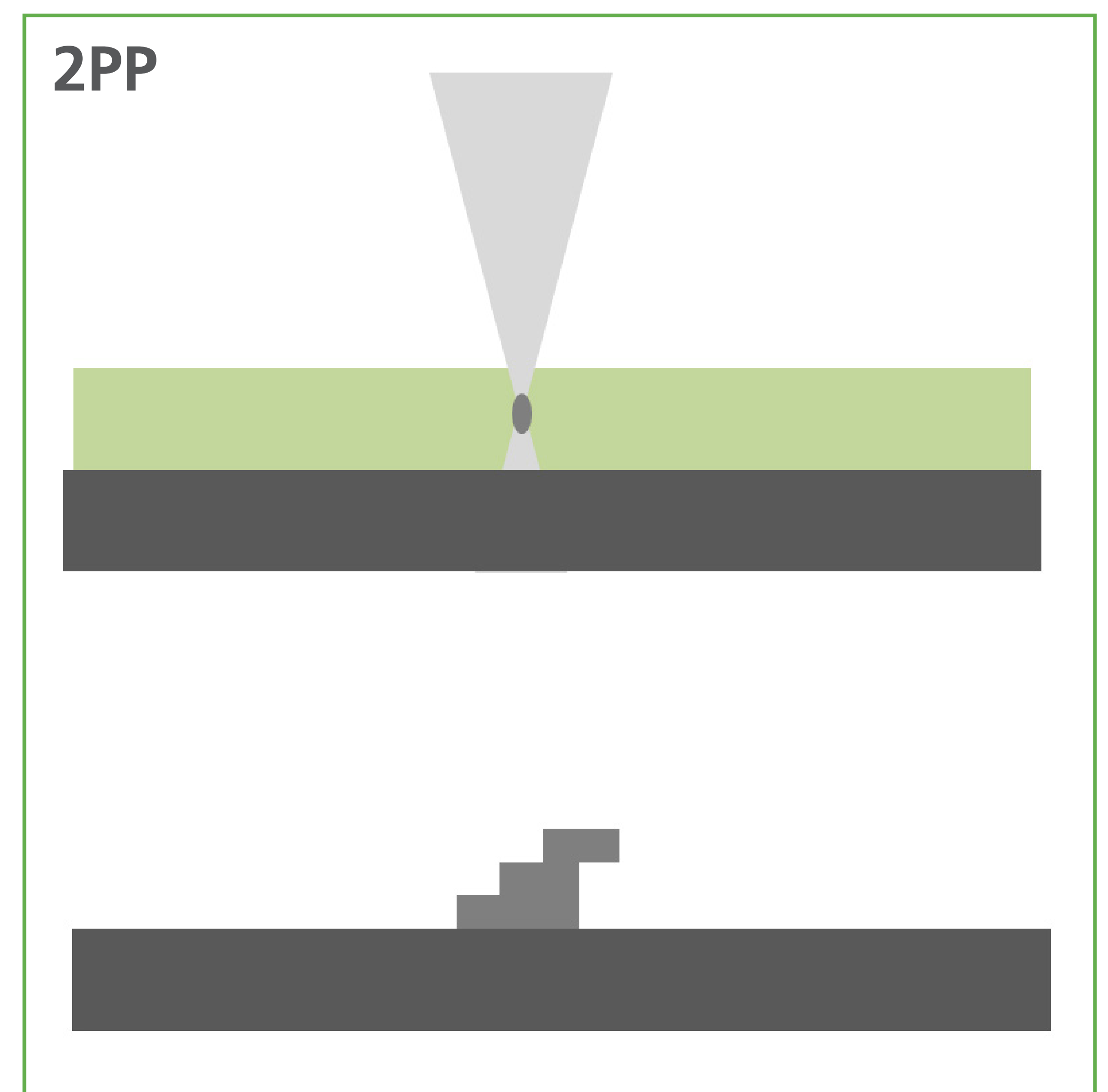
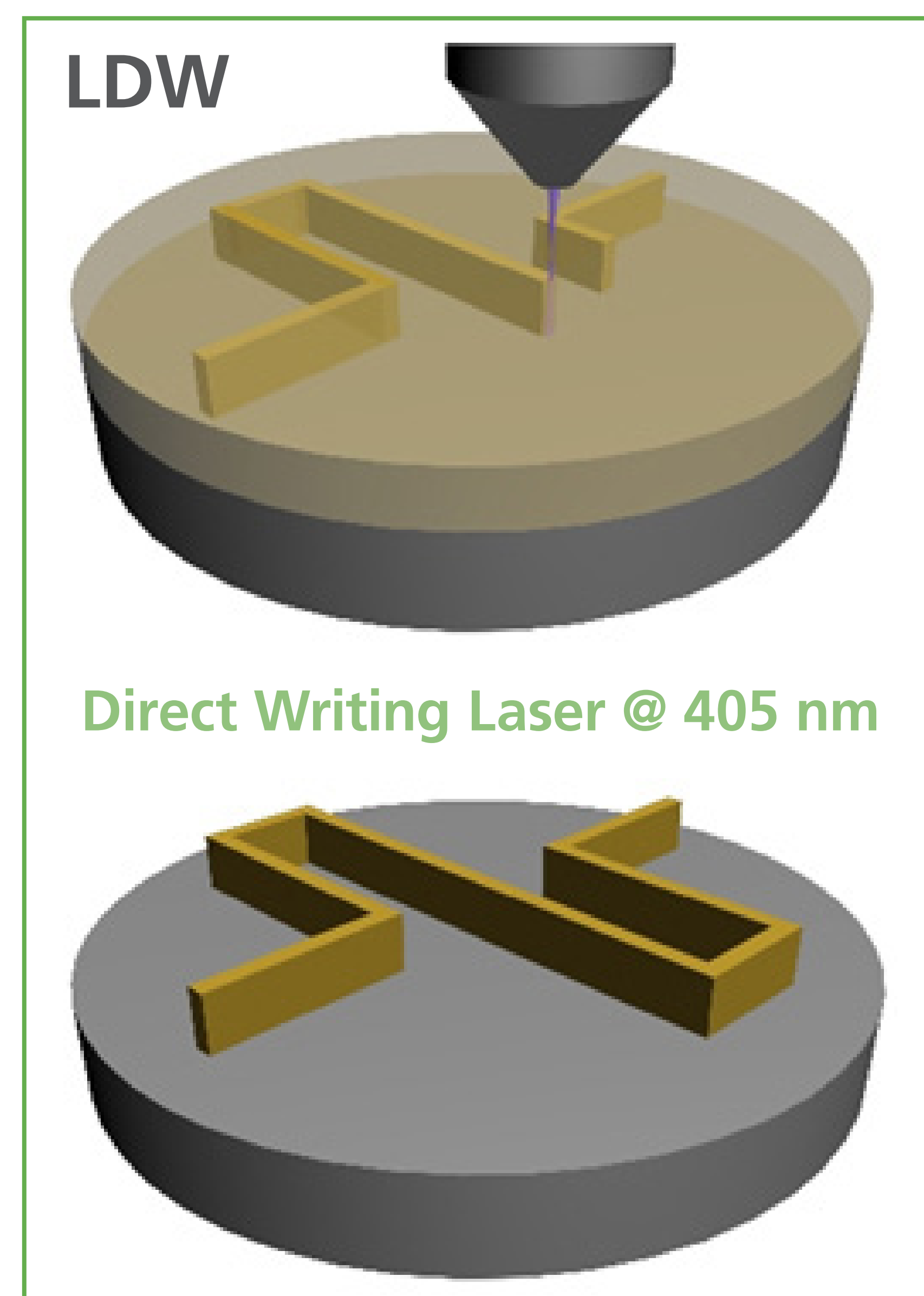


40  $\mu\text{m}$  thick mr-DWL, rod pattern <sup>2</sup>

## Unique features

- Specifically designed for exposure wavelengths above 400 nm
- Suitable for DLW (e.g. @ 405 nm) & 2PP
- High sensitivity
- Excellent thermal and chemical stability
- High wet and dry etch stability

## Process schematics



## Applications

- Fast and contactless prototyping by DLW & 2PP
- Etch mask for wet and dry etch processes
- Mould for electroplating
- Mould for stamp fabrication by thermal or UV moulding
- Optical applications in micro systems technology

## Technical data

Resist		mr-DWL 5	mr-DWL 40	mr-DWL 100
Film thickness	$\mu\text{m}$	3 - 12	20 - 100	20 - 150

